

# **Product Summary**

V <sub>(BR)DSS</sub>	R <sub>DS(on)TYP</sub>	I <sub>D</sub>	
85V	4.5mΩ@10V	110A	



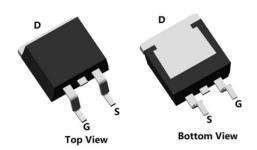
### **Feature**

- Fast Switching
- Low Gate Charge and Rdson
- Advanced Split Gate Trench Technology
- 100% Single Pulse avalanche energy Test

# **Applications**

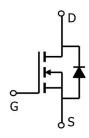
- Power switching application
- DC-DC Converter
- Power Management

### **Package**

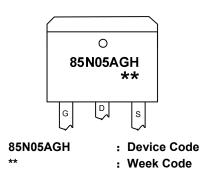


TO-263(1:G 2:D 3:S)

### Circuit diagram



# Marking



### **Order Information**

Device	Package	Unit/Tape
SP85N05AGHTD	TO-263	800

85V N-Channel Power MOSFET

# Absolute maximum ratings (Ta=25°C unless otherwise noted)

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V <sub>DS</sub>	85	V
Gate-Source Voltage	V <sub>GS</sub>	±20	V
Continuous Drain Current (Tc=25°C)	I <sub>D</sub>	110	Α
Continuous Drain Current (Tc=100°C)	I <sub>D</sub>	75	Α
Pulsed Drain Current	I <sub>DM</sub>	440	Α
Single Pulse Avalanche Energy <sup>1</sup>	Eas	784	mJ
Power Dissipation (Tc=25°C)	P <sub>D</sub>	170	W
Thermal Resistance Junction-to-Case	R <sub>θJC</sub>	0.74	°C/W
Storage Temperature Range	T <sub>STG</sub>	-55 to 150	°C
Operating Junction Temperature Range	TJ	-55 to 150	$^{\circ}$ C

# Electrical characteristics (Ta=25°C, unless otherwise noted)

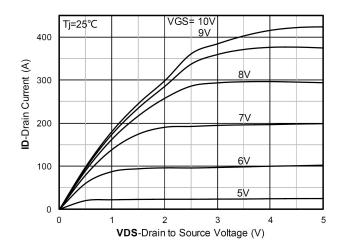
Characteristics	Symbol	Test Condition	Min	Тур	Max	Unit	
Static Characteristics							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	ID = 250µA, VGS = 0V	85	90	-	V	
Drain Cut-Off Current	I <sub>DSS</sub>	VDS = 68V, VGS = 0V	-	-	1		
Gate Leakage Current	I <sub>GSS</sub>	VGS = ±20V, VDS = 0V	-	-	±0.1	μA	
Gate Threshold Voltage	$V_{GS(th)}$	VDS = VGS, ID = 250μA	2	3	4	V	
Drain-Source ON Resistance	R <sub>DS(ON)</sub>	VGS = 10V, ID = 20A	-	4.5	5.7	mΩ	
Dynamic Characteristics							
Input Capacitance	Ciss		-	3543	-		
Output Capacitance	Coss	VDS =40V, VGS = 0V, f = 1.0MHz	-	1058	-	pF	
Reverse Transfer Capacitance	C <sub>rss</sub>		-	23	-		
Total Gate Charge	Qg	VDS=40V , VGS=10V , ID=165A	-	49	-	nC	
Gate-Source Charge	Q <sub>gs</sub>		-	16	-		
Gate-Drain Charge	$Q_{gd}$	1		13	-		
Switching Characteristics	_						
Turn-On Delay Time	t <sub>d(on)</sub>		-	17	-		
Rise Time	t <sub>r</sub>	VGS = 10V, VDS = 40V, ID=165A,	-	25	-	nS	
Turn-Off Delay Time	$t_{d(off)}$	RG = 1.6Ω	-	36	-		
Fall Time	t <sub>f</sub>		-	15	-		
Drain-Source Body Diode Characteristics							
Source-Drain Diode Forward Voltage	$V_{SD}$	$I_S = 1A$ , $V_{GS} = 0V$	-	-	1.2	V	
Maximum Body-Diode Continuous Current	Is		-	-	110	Α	
Reverse Recovery Time	Trr	I <sub>S</sub> =20A, di/dt=100A/us, TJ=25℃		62	-	nS	
Reverse Recovery Charge	Q <sub>rr</sub>			103	-	nC	

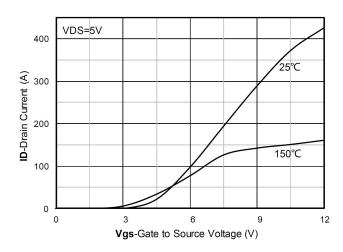
#### Note:

**1.** The test condition is VDD=45V,VGS=10V,L=0.5mH,RG=25 $\Omega$ 

### **85V N-Channel Power MOSFET**

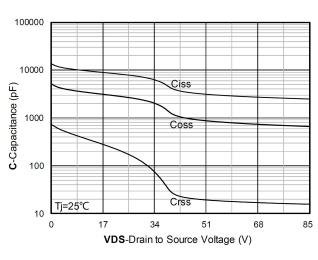
# **Typical Characteristics**

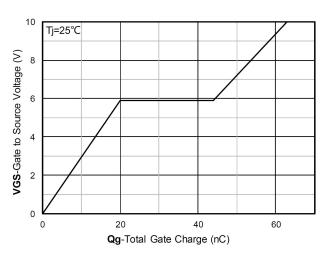




#### **Output Characteristics**

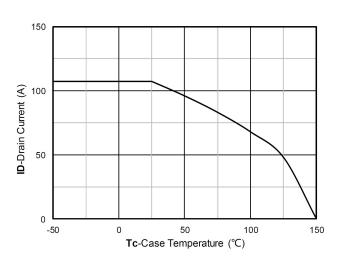


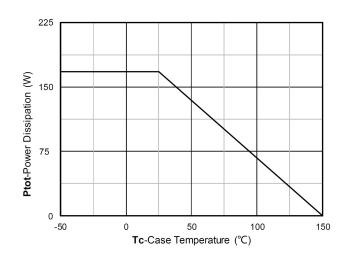




#### Capacitance Characteristics

**Gate Charge** 

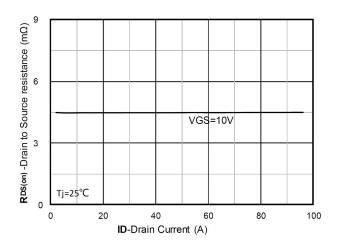


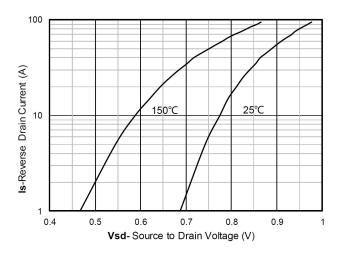


**Current dissipation** 

Power dissipation

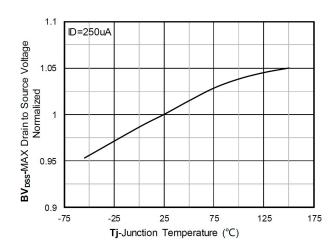


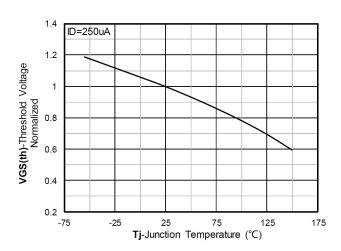




RDS(on) VS Drain Current

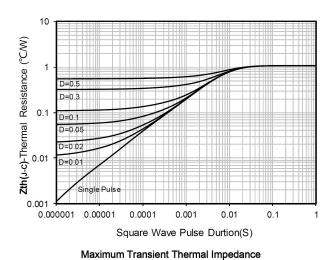
Forward characteristics of reverse diode

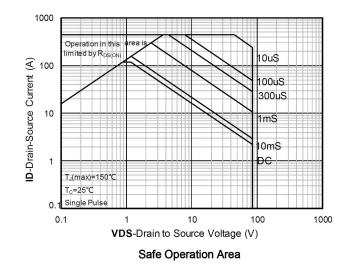




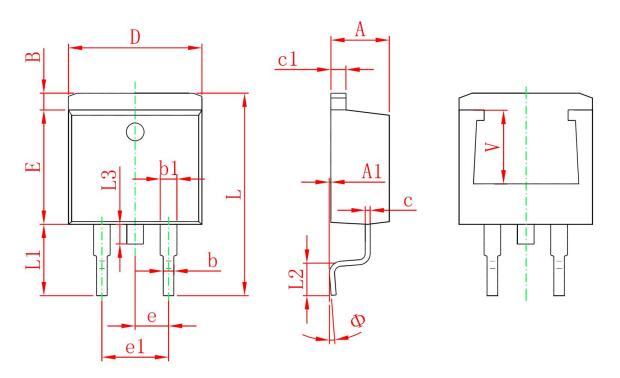
Normalized breakdown voltage

Normalized Threshold voltage





# TO-263 Package Information



	Dimensions	In Millimeters	Dimension	s In Inches	
Symbol	Min.	Max.	Min.	Max.	
Α	4.470	4.670	0.176	0.184	
A1	0.000	0.150	0.000	0.006	
В	1.120	1.420	0.044	0.056	
b	0.710	0.910	0.028	0.036	
b1	1.170	1.370	0.046	0.054	
С	0.310	0.530	0.012	0.021	
c1	1.170	1.370	0.046	0.054	
D	10.010	10.310	0.394	0.406	
Е	8.500	8.900	0.335	0.350	
е	2.540	2.540 TYP.		0.100 TYP.	
e1	4.980	5.180	0.196	0.204	
L	14.940	15.500	0.588	0.610	
L1	4.950	5.450	0.195	0.215	
L2	2.340	2.740	0.092	0.108	
L3	1.300	1.700	0.051	0.067	
Ф	0°	8°	0°	8°	
V	5.600 REF.		0.220	REF.	